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		机密等级 Confidential	B		
技术文件 Technical	Sanan Semiconductor SDS065J010E3 规格书 Sanan Semiconductor SDS065J010E3 Datasheet	版别 Rev. No.	2.0.0	生效日期 Effective Date	2025/12/26

Sanan Semiconductor

SDS065J010E3 Datasheet Ver. 2.0.0

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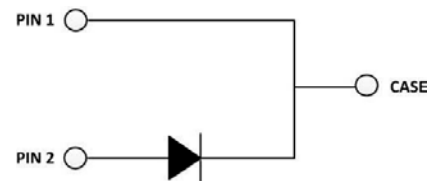
文件制/修订纪录 Revision History				
版本 Version	制(修)订者 Reviser	制(修)订日期 Date	变更章节 Change Sec.	修 改 说 明 Description
1.0.0	曹文长	2022/08/28	ALL	初版发行
1.0.1	赵为国	2022/12/19	Package	更新 Dimension
1.0.2	曹文长	2023/05/09	页眉	更新文件编号
1.1.0	赵为国	2023/06/12	ALL	更新为新模板
1.1.1	赵为国	2024/05/04	Electrical Characteristic Diagrams	Figure 2.纵坐标单位 uA 修改为 μ A Figure 6.纵坐标单位 nJ 修改为 μ J
			Important Notices – Read Carefully	更新为新版本，去除 hunan 字样
			Warning	更新为新版本，去除 hunan 字样
			页脚	更新为新版本，去除 hunan 字样
1.1.2	李锦绩	2024/07/19	Table 1. Maximum Ratings	新增 IFmax
			Electrical Characteristic Diagrams	新增热阻曲线
2.0.0	吴婷	2025/12/26	Package Information	更新为委外代厂 POD

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3rd Generation 650V/10A SiC Schottky Barrier Diode

Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55°C to 175°C
- RoHS compliant



Package Type: TO-263-2L



Potential Applications

- Industrial power supplies: Industrial UPS
- Battery chargers
- Solar inverters
- Switch mode power supplies

Description

The SDS065J010E3 SiC Schottky Barrier Diode (SBD) has been developed using Sanan's advanced 3rd generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 650V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

Product Specifications

Device	V_{RRM}	I_F (135°C)	V_F (25°C)	Q_C	Marking
SDS065J010E3	650V	15A	1.30V	29nC	DS065010E3

CONTENTS

Features.....	1
Potential Applications.....	1
Description.....	1
Product Specifications	1
Table 1 Maximum Ratings.....	3
Table 2 Thermal Resistance.....	3
Table 3 Static Electrical Characteristics.....	4
Table 4 Dynamic Electrical Characteristics	4
Electrical Characteristic Diagrams.....	5
Package Information	7
Recommended Solder Pad Layout.....	8
Ordering Information	8
Important Notices – Read Carefully	9
Warning	9

Table 1. Maximum Ratings

(T_C = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V _{RRM}	650	V	T _C = 25°C
Surge peak reverse voltage	V _{RSM}	650		T _C = 25°C
DC reverse voltage	V _{DC}	650		T _C = 25°C
Continuous forward current	I _F	30	A	T _C = 25°C
		15		T _C = 135°C
		10		T _C = 155°C
Surge non-repetitive forward current	I _{FSM}	80	A	T _C = 25°C, t _p = 10ms, half sine pulse
Non-repetitive peak forward current	I _{F,Max}	500	A	T _C = 25°C, t _p = 10μs, pulse
Surge repetitive forward current	I _{FRM}	54	A	T _C = 25°C, t _p = 10ms, half sine wave D = 0.1
Power dissipation	P _{tot}	120	W	T _C = 25°C
i ² t value	∫i ² dt	32	A ² s	T _C = 25°C, t _p = 10ms
Operating junction temperature	T _j	-55~175	°C	
Storage temperature	T _{stg}	-55~175	°C	

Table 2. Thermal Resistance

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	R _{th(j-c)}	/	1.24	/	°C/W	

Table 3. Static Electrical Characteristics

($T_j = 25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	650	/	/	V	$I_R = 100\ \mu\text{A}$
Forward voltage	V_F	/	1.30	1.50	V	$I_F = 10\text{A}$, $T_j = 25^{\circ}\text{C}$
		/	1.55	1.80		$I_F = 10\text{A}$, $T_j = 175^{\circ}\text{C}$
Reverse current	I_R	/	1	30	μA	$V_R = 650\text{V}$, $T_j = 25^{\circ}\text{C}$
		/	3	80		$V_R = 650\text{V}$, $T_j = 175^{\circ}\text{C}$

Table 4. Dynamic Electrical Characteristics

($T_j = 25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	556	/	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$
		/	55	/		$V_R = 200\text{V}$, $f = 1\text{MHz}$
		/	45	/		$V_R = 400\text{V}$, $f = 1\text{MHz}$
Total capacitive charge	Q_C	/	29	/	nC	$V_R = 400\text{V}$
Capacitance stored energy	E_C	/	4.3	/	μJ	$V_R = 400\text{V}$

Electrical Characteristic Diagrams

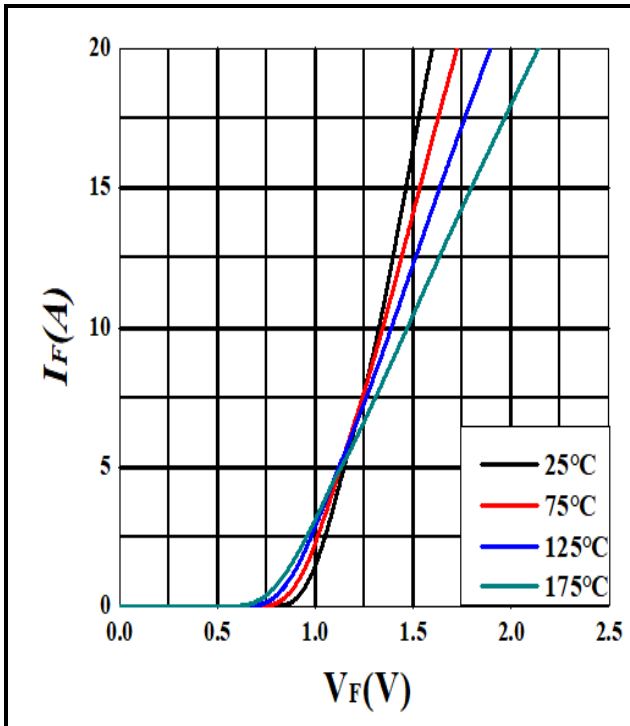


Figure 1. Forward characteristics

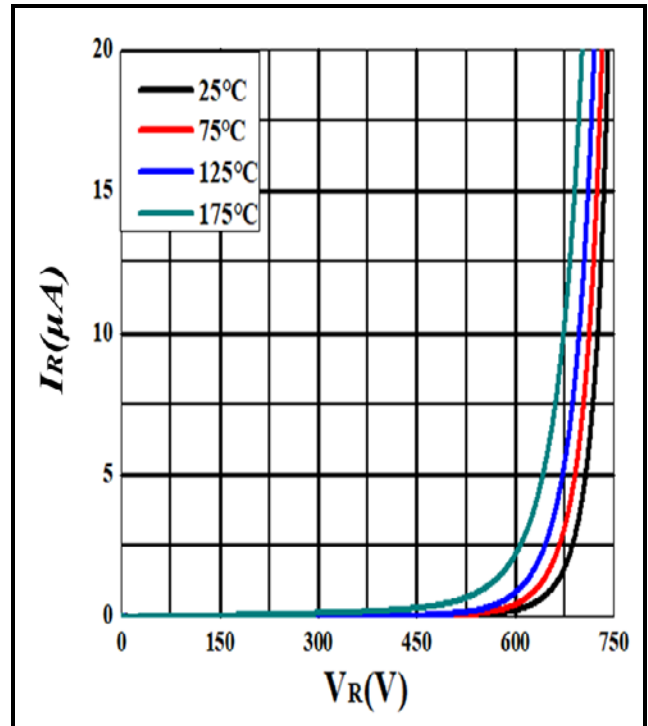


Figure 2. Reverse characteristics

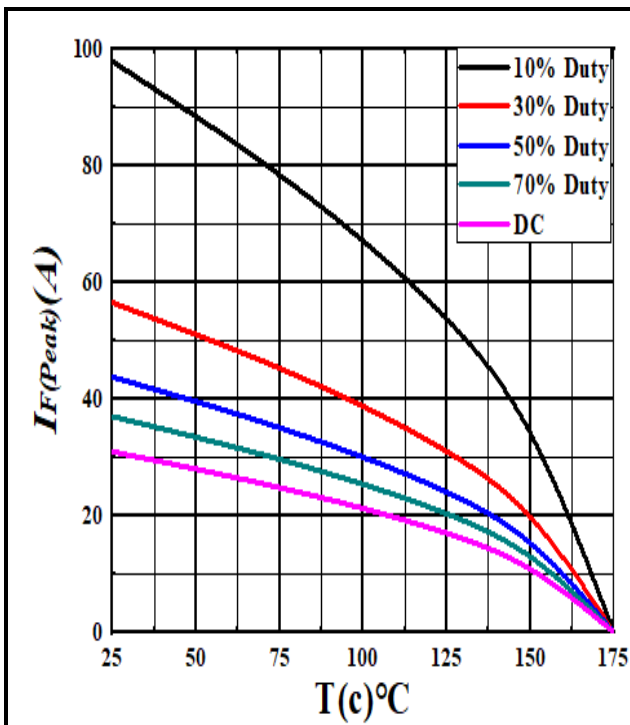


Figure 3. Current derating

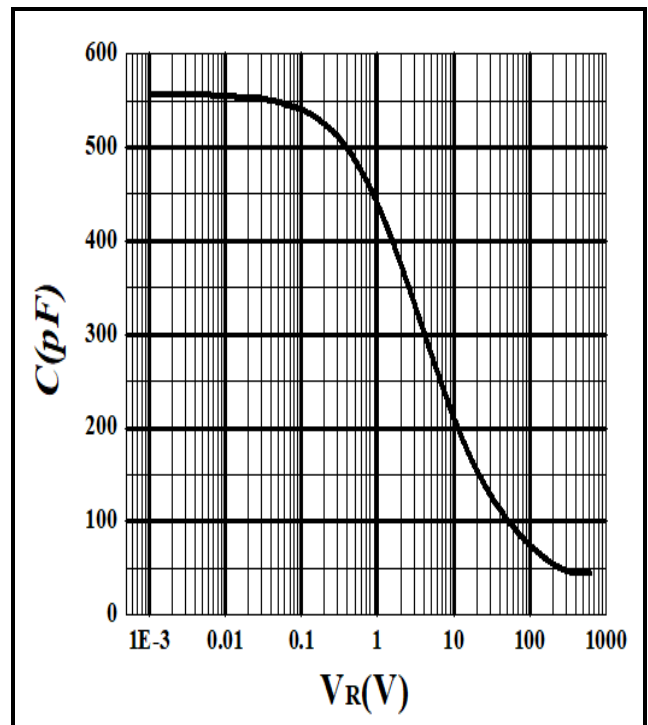


Figure 4. Capacitance vs. reverse voltage

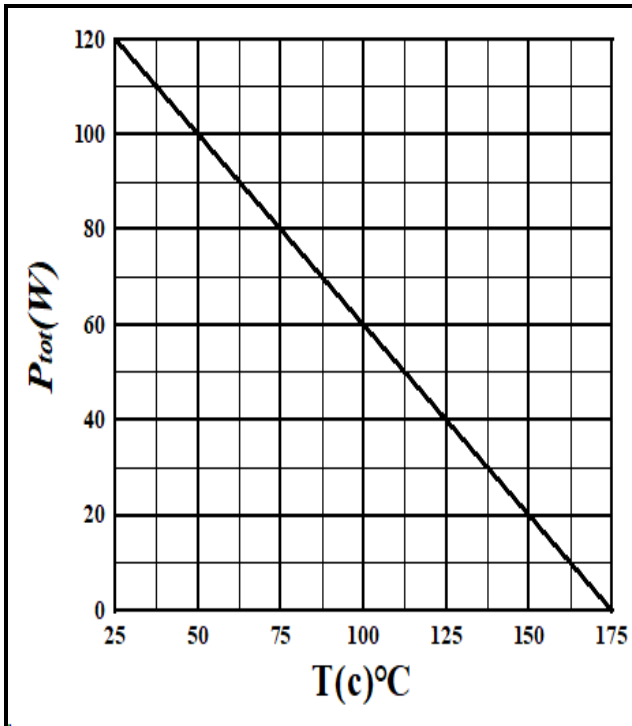


Figure 5. Power derating

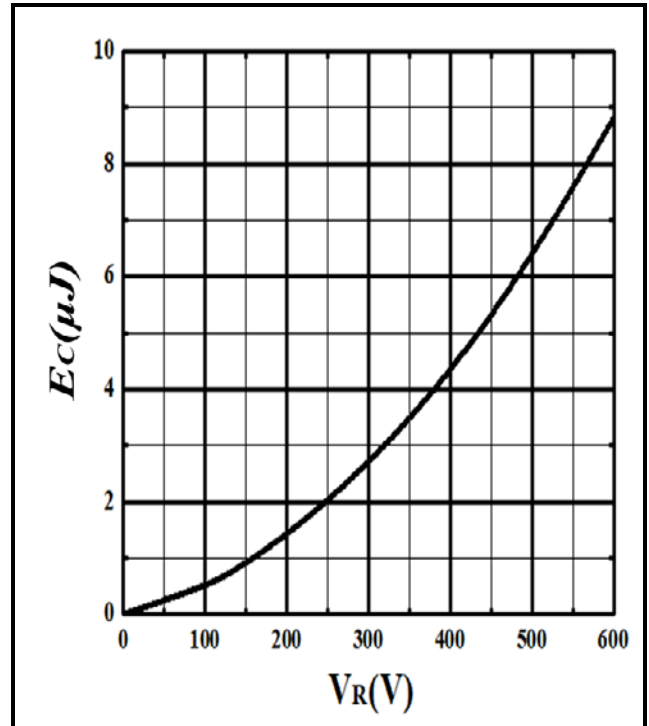


Figure 6. Capacitance stored energy

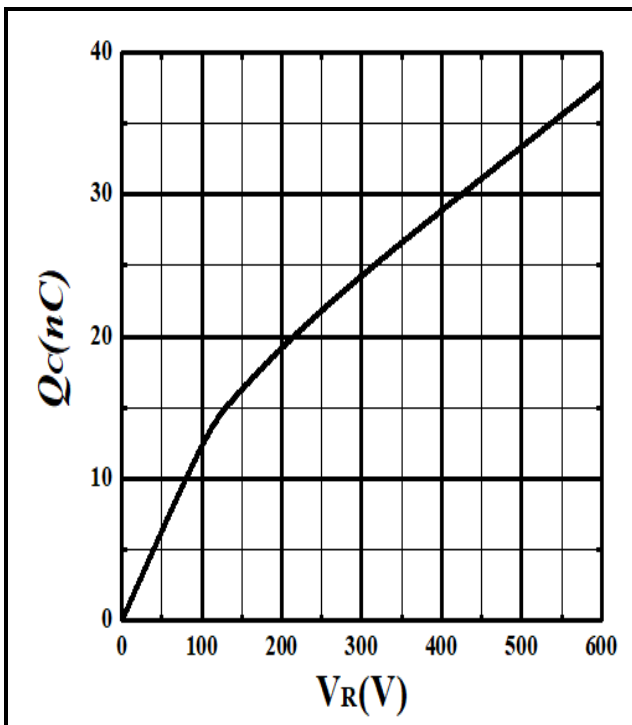


Figure 7. Total capacitance charge vs. reverse voltage

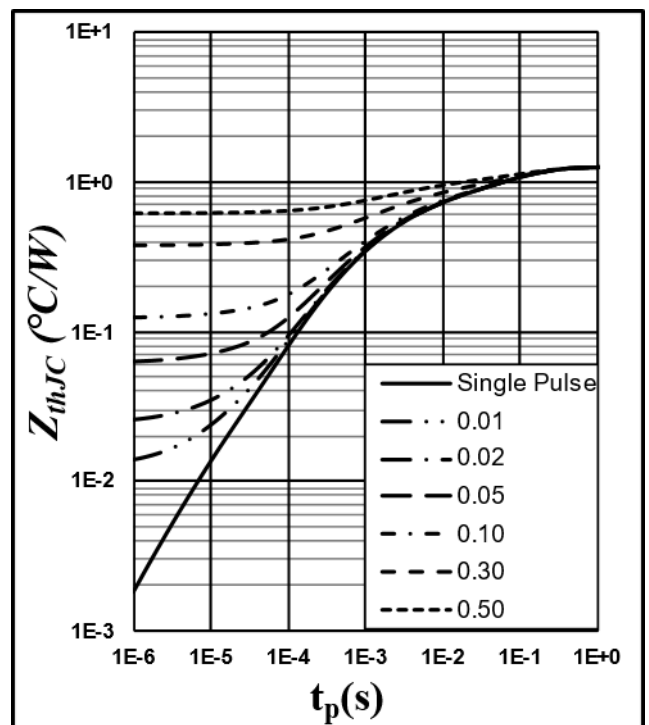
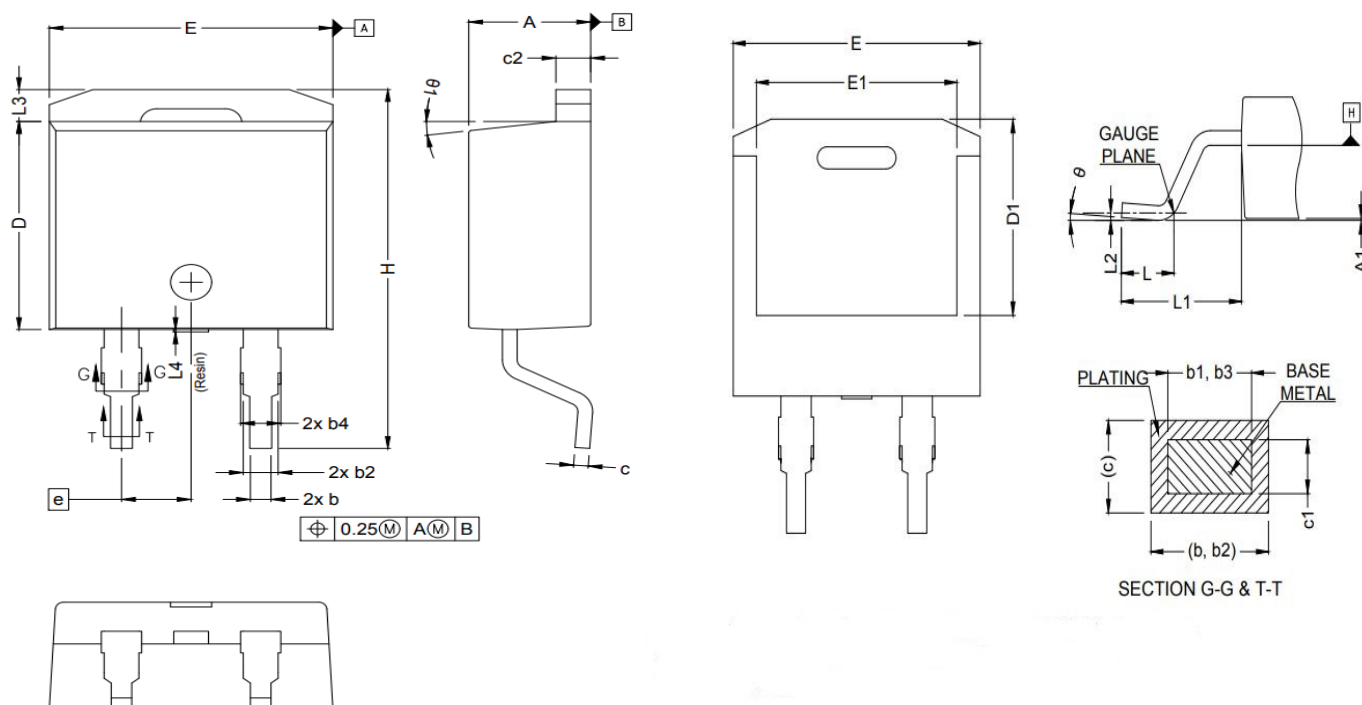


Figure 8. Transient Thermal Impedance
(Junction - Case)

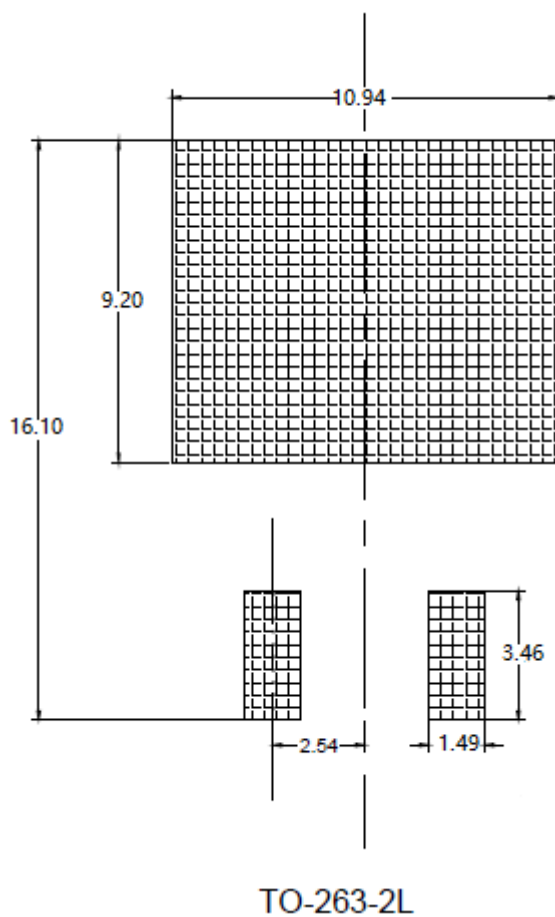
Package Information



Symbol	Min	Max	Symbol	Min	Max
A	4.36	4.56	E	10.15	10.55
A1	0.00	0.25	E1	8.10	8.70
b	0.70	0.90	e	2.54 BSC	
b1	0.51	0.89	H	15.00	15.60
b2	1.20	1.46	L	1.90	2.50
b3	1.17	1.37	L1	4.78	5.28
b4	1.20	1.57	L2	0.25 TYP	
c	0.38	0.69	L3	1.05	1.65
c1	0.38	0.53	L4	0	0.50
c2	1.19	1.34	θ	0°	10°
D	8.60	9.00	θ 1	0°	15°
D1	6.90	7.50			

Recommended Solder Pad Layout

Note: All dimensions are in mm



Ordering Information

Part number	SDS065J010E3-ISARH
Package	TO-263-2L
Unit quantity	800 EA
Packing type	Tape & Reel

Important Notices – Read Carefully

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